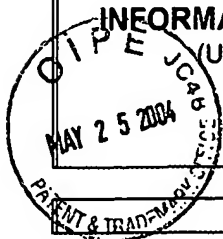


INFORMATION DISCLOSURE CITATION (Use several sheets if necessary) PTO Form 1449	Attorney Docket No. 60999-181	Serial No. 10/783,825
	Applicants Krutko et al.	
	Filing Date February 20, 2004	Group 2817 2819



U.S. PATENT DOCUMENTS

*Examiner Initial	Document Number	Date	Name	Class	Sub Class	Filing Date
	A01					
	A02					
	A03					

FOREIGN PATENT DOCUMENTS

FOREIGN-ENTRY DOCUMENTS								
		Document Number	Date	Country	Class	Sub Class	<u>Translation</u> YES NO	
	B01							
	B02							

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